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SOT-23

SSCN847BGS6

NPN Switching Transistor

> Features

VCB	VCE	VEB	VCESAT	IC
50V	45V	6V	500mV	100mA

> Description

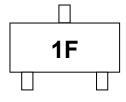
The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-23 package, which is designed for telephony and professional communication equipment.

1 - Base 2 - Emitter

Pin configuration

 \triangleright

Circuit Diagram



Marking (Top View)

General purpose switching and amplification

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Applications

• Telephony and professional communication equipment

Ordering Information

Device	Package	Shipping
SSCN847BGS6	SOT-23	3000/Reel



SSCN847BGS6

> Absolute Maximum Ratings($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector- Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	lc	100	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

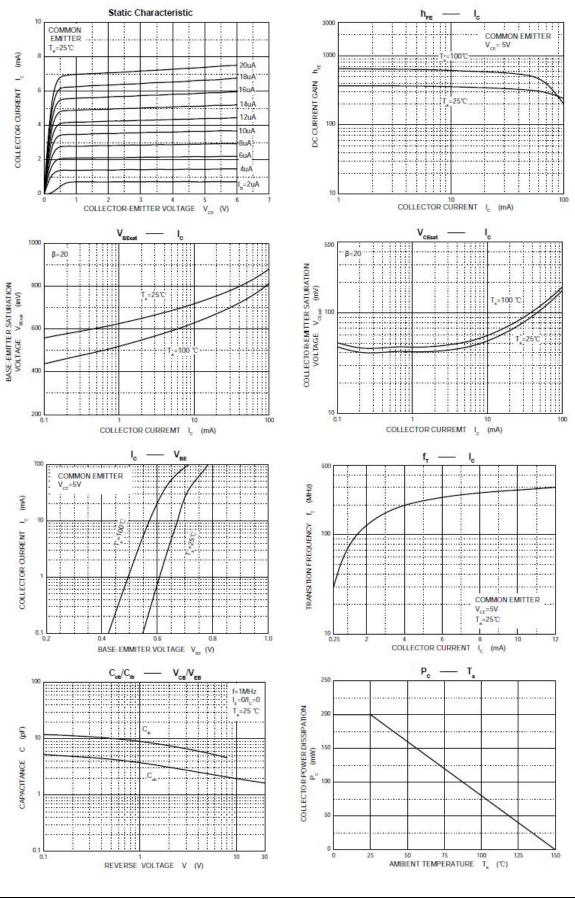
> Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	ВV _{сво}	I _C =10uA, I _E =0	50			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =10mA, I _B =0	45			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =10uA, I _C =0	6			V
Collector Cutoff Current	I _{СВО}	V _{CB} =50V, I _E =0			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0			100	nA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =2mA	200		450	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =100mA, I _B =5mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE (sat)}	I _C =100mA, I _B =5mA			1.1	V
Collector Output Capacitance	Cob	V _{CB} =10V, f=1MHz			4.5	pF



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> Typical Performance Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

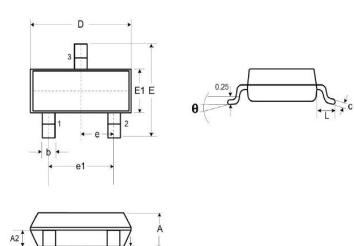


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Max.

Package Information



Α	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.51
С	0.08	-	0.18
D	2.80	2.90	3.04
Е	2.10	2.37	2.64
E1	1.20	1.30	1.40
e1	1.90		
е	0.95		
L	0.40	0.50	0.60
L1	0.55		
N	3		
θ	0°	-	8°

Millimeters

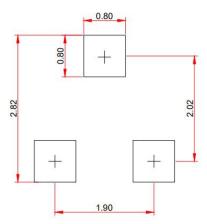
Тур.

DIM

Min.

Recommended Pad outline (Unit: mm)

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